L	Hits	Search Text	DB	Time stamp
Number	urca			
1	0	5519241.pn. and (thyristor same	USPAT;	2004/11/04
]	semiconductor) and (doped adj emitter)	US-PGPUB;	10:30
		and (doped adj well) and (control adj port)	EPO; JPO; DERWENT	
2	o	(thyristor same semiconductor) and	USPAT;	2004/11/04
2	°	@ad<20021028 and (doped adj emitter) and	US-PGPUB;	10:31
		(doped adj well) and (carrier adj	EPO; JPO;	
		coupler)	DERWENT	
3	0	(thyristor same semiconductor) and	USPAT;	2004/11/04
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	10:32
		(doped adj well) and (carrier adj coupler) and (control adj port)	EPO; JPO; DERWENT	
4	o	(thyristor same semiconductor) and	USPAT;	2004/11/04
•	-	@ad<20021028 and (doped adj emitter) and	UŞ-PGPUB;	10:33
		(doped adj well) and (carrier same	EPO; JPO;	
		drain\$3) and (control adj port)	DERWENT	
5	0	(thyristor same semiconductor) and	USPAT;	2004/11/04
		@ad<20021028 and (doped adj emitter) and (doped adj well) and (carrier\$2 same	US-PGPUB; EPO; JPO;	10:33
		(doped adj well) and (carrier\$2 same drain\$3) and (control adj port)	DERWENT	
6	. 0	(thyristor same semiconductor) and	USPAT;	2004/11/04
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	10:34
		(doped adj well) and (carrier\$2 same	EPO; JPO;	
_		contact) and (control adj port)	DERWENT	2004/11/04
7	0	(thyristor same semiconductor) and @ad<20021028 and (emitter) and (doped adj	USPAT; US-PGPUB;	2004/11/04
		well) and (carrier\$2 same contact) and	EPO; JPO;	10.55
	,	(control adj port)	DERWENT	
8	0	(thyristor same semiconductor) and	USPAT;	2004/11/04
		@ad<20021028 and (emitter) and (doped adj	US-PGPUB;	10:37
		well) and (carrier\$2 same (contact or	EPO; JPO;	
	0	drain\$3)) and (control adj port) (thyristor same semiconductor) and	DERWENT USPAT;	2004/11/04
9	0	(thyristor same semiconductor) and (doped adj	US-PGPUB;	10:37
]		well) and (carrier\$2 same (contact or	EPO; JPO;	
		drain\$3 or well)) and (control adj port)	DERWENT	
_	70354	thyristor	USPAT;	2004/10/18
	;	·	US-PGPUB; EPO; JPO;	15:21
			DERWENT	
	10634	thyristor same semiconductor	USPAT;	2004/10/18
	10001		US-PGPUB;	15:21
		•	EPO; JPO;	
-		l	DERWENT	2004/10/10
-	7517	(thyristor near8 semiconductor) anmd	USPAT; US-PGPUB;	2004/10/18
			EPO; JPO;	13.11
[.]			DERWENT	
-	2	6756612.pn.	USPAT;	2004/10/18
			US-PGPUB;	15:28
		·	EPO; JPO;	
_	6559	(thyristor near8 semiconductor) and	DERWENT USPAT;	2004/10/18
-	0009	(thyristor hears semiconductor) and @ad<20021028	US-PGPUB;	15:49
			EPO; JPO;	
			DERWENT	
-	41	(thyristor near8 semiconductor) and	USPAT;	2004/10/18
		@ad<20021028 and (doped adj emitter)	US-PGPUB; EPO; JPO;	15:50
			DERWENT	
_	_ 1	(thyristor near8 semiconductor) and	USPAT;	2004/11/03
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	09:24
		(doped adj well)	EPO; JPO;	
1			DERWENT	2004/10/10
-	2	(thyristor same semiconductor) and Gad<20021028 and (doped adj emitter) and	USPAT; US-PGPUB;	2004/10/18 15:51
		(doped adj well)	EPO; JPO;	13.31
		(40,000 00) 11044/	DERWENT	

-	0	(thyristor same semiconductor) and	USPAT;	2004/10/18
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	15:53
		(doped adj well) and (carrier asd	EPO; JPO;	
	_	coupler) and (carrier adj drainage)	DERWENT	0004/10/10
-	0	(thyristor same semiconductor) and	USPAT;	2004/10/18
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	15:53
		(doped adj well) and (carrier asd	EPO; JPO;	
		coupler) and (control adj port)	DERWENT	
·	0		USPAT;	2004/10/18
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	15:54
		(doped adj well) and (carrier adj	EPO; JPO;	
		coupler) and (control adj port)	DERWENT	
-	2		USPAT;	2004/11/04
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	10:30
		(doped adj well) and (carrier asd	EPO; JPO;	
		coupler)	DERWENT	
-	0		USPAT;	2004/10/18
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	15:59
		(doped adj well) and (control adj port)	EPO; JPO;	
			DERWENT	0004/10/10
[-	2	(thyristor same semiconductor) and	USPAT;	2004/10/18
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	16:02
		(doped adj well) and (carrier asd	EPO; JPO;	
		coupler) and control	DERWENT	
-	0	(thyristor same semiconductor) and	USPAT;	2004/11/01
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	13:27
ļ		(doped adj well) and (carrier and	EPO; JPO;	
		coupler) and control	DERWENT	
-	.0	(thyristor same semiconductor) and	USPAT;	2004/10/18
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	16:07
		(doped adj well) and (carrier adj	EPO; JPO;	
		coupler) and control	DERWENT	
-	. 0		USPAT;	2004/10/18
		semiconductor) and @ad<20021028 and	US-PGPUB;	16:09
		(doped adj emitter) and (doped adj well)	EPO; JPO;	ļ
		and (carrier adj coupler) and control	DERWENT	0004/10/10
-	0	6756612.ccls. and (thyristor same	USPAT;	2004/10/18
		semiconductor) and @ad<20021028 and	US-PGPUB;	16:11
		(doped adj emitter) and (doped adj well)	EPO; JPO;	
		and (carrier adj coupler) and (control	DERWENT	i
	_	adj port)		2004/10/19
-	0	6756612.ccls. and (thyristor same	USPAT;	2004/10/18 16:12
		semiconductor) and @ad<20021020 and	US-PGPUB;	16:12
		(doped adj emitter) and (doped adj well)	EPO; JPO;	
		and (carrier adj coupler) and (control	DERWENT	
	1	adj port)	TICDATE.	2004/10/18
-	0	6756612.ccls. and (thyristor same	USPAT;	16:12
		semiconductor) and (doped adj emitter)	US-PGPUB;	10.12
		and (doped adj well) and (carrier adj	EPO; JPO;	
i		coupler) and (control adj port)	DERWENT USPAT;	2004/10/18
-	1	6756612.pn. and (thyristor same	US-PGPUB;	16:12
		semiconductor) and (doped adj emitter)	EPO; JPO;	10.12
		and (doped adj well) and (carrier adj	DERWENT	
	1 ^	coupler) and (control adj port) 6756612.pn. and (thyristor same	USPAT;	2004/10/18
-	0		US-PGPUB;	16:14
		semiconductor) and (doped adj emitter) and (doped adj well) and (carrier adj	EPO; JPO;	10.13
	ļ	and (doped adj well) and (carrier adj coupler) and (control adj port) and	DERWENT	1
		Coupler) and (control adj port) and @ad<20021028	DELIMINA	·
1_	0	1	USPAT;	2004/10/18
1	1	semiconductor) and (doped adj emitter)	US-PGPUB;	16:15
		and (doped adj well) and (carrier adj	EPO; JPO;	
}		coupler) and (control adj port) and	DERWENT	
		Coupler, and (Control ad) port, and Cad<20021027		
_	0	1 7	USPAT;	2004/10/18
		semiconductor) and (doped adj emitter)	US-PGPUB;	16:15
		and (doped adj well) and (carrier adj	EPO; JPO;	
		coupler) and (control adj port) and	DERWENT	
1		@ad<20021006	1	•
i	1	1	<u> </u>	

-	0	6756612.pn. and (thyristor same	USPAT;	2004/10/18
		semiconductor) and (doped adj emitter)	US-PGPUB;	16:18
1		and (doped adj well) and (carrier adj	EPO; JPO; DERWENT	
ŀ		coupler) and (control adj port) and @ad<20021025	DERWENT	
_	1	6756612.pn. and (thyristor same	USPAT;	2004/10/18
		semiconductor) and (doped adj emitter)	US-PGPUB;	16:19
1		and (doped adj well) and (carrier adj	EPO; JPO;	
		coupler) and (control adj port) and	DERWENT	
		@ad<20021030		
-	1	6756612.pn. and (thyristor same	USPAT;	2004/10/18
		semiconductor) and (doped adj emitter)	US-PGPUB;	16:19
		and (doped adj well) and (carrier adj	EPO; JPO;	
		coupler) and (control adj port) and	DERWENT	
		@ad<20021029	USPAT;	2004/10/18
-	0	6756612.pn. and (thyristor same semiconductor) and (doped adj emitter)	US-PGPUB;	16:20
		and (doped adj well) and (carrier adj	EPO; JPO;	10.20
		coupler) and (control adj port) and	DERWENT	
·		@ad<20021028		
-	1	6756612.pn. and (thyristor same	USPAT;	2004/10/18
		semiconductor) and (doped adj emitter)	US-PGPUB;	16:20
1		and (doped adj well) and (carrier adj	EPO; JPO;	
		coupler) and (control adj port) and	DERWENT	
	_ [@ad<20021029	Henam.	2004/10/19
[-	2	6756612.pn. and (carrier adj coupler)	USPAT; US-PGPUB;	09:52
<u> </u>			EPO; JPO;	05.52
			DERWENT	
_	o	(thyristor same semiconductor) and	USPAT;	2004/10/19
		@ad<20021028 and (doped adj emitter) and	US-PGPUB;	11:30
,		(doped adj well) and (control adj port)	EPO; JPO;	
			DERWENT	
-	1	(thyristor same semiconductor) and	USPAT;	2004/10/19
		@ad<20021029 and (doped adj emitter) and	US-PGPUB;	11:33
		(doped adj well) and (control adj port)	EPO; JPO; DERWENT	•
	1	(thyristor same semiconductor) and (doped	USPAT;	2004/10/19
-	_	adj emitter) and (doped adj well) and	US-PGPUB;	12:33
		(control adj port)	EPO; JPO;	
			DERWENT	
_	2	6229161.pn.	USPAT;	2004/10/19
			US-PGPUB;	11:55
			EPO; JPO; DERWENT	
	,	6104045 pp	USPAT;	2004/10/19
-	2	6104045.pn.	US-PGPUB;	11:57
	·		EPO; JPO;	
			DERWENT	
-	2	4797373.pn.	USPAT;	2004/10/19
			US-PGPUB;	11:59
			EPO; JPO;	
		6225165 mm	DERWENT USPAT;	2004/10/19
-	2	6225165.pn.	US-PGPUB;	12:01
1.			EPO; JPO;	
]		DERWENT	
-	2	5528062.pn.	USPAT;	2004/10/19
			US-PGPUB;	12:02
			EPO; JPO;	
	_	5528062.pn. and (control adj port)	DERWENT USPAT;	2004/10/19
-	0	5526062.pn. and (control adj port)	US-PGPUB;	12:03
	İ		EPO; JPO;	
			DERWENT	
-	0	5132767.pn. and (control adj port)	USPAT;	2004/10/19
			US-PGPUB;	12:03
			EPO; JPO;	
			DERWENT	

_	2	5132767.pn.	USPAT;	2004/10/19
			US-PGPUB;	12:03
			EPO; JPO;	
			DERWENT	
l -	2	6084274.pn.	USPAT;	2004/10/19
	_		US-PGPUB;	12:04
			EPO; JPO;	
			DERWENT	
	2	5600160.pn.	USPAT;	2004/10/19
-		5800180.pii.	US-PGPUB;	12:04
				12.04
			EPO; JPO;	
			DERWENT	0004/10/10
-	2	6545297.pn.	USPAT;	2004/10/19
			US-PGPUB;	12:05
			EPO; JPO;	
		'	DERWENT	
_	0	6545297.pn. and (control adj port)	USPAT;	2004/10/19
		• • •	US-PGPUB;	12:05
			EPO; JPO;	
			DERWENT	ł
_	2	6583452.pn.	USPAT;	2004/10/19
		0005452.pm.	US-PGPUB;	12:10
			EPO; JPO;	• - •
			DERWENT	
	_	(502452 mm and /		2004/10/19
_	1	6583452.pn. and (control adj port)	USPAT;	1
			US-PGPUB;	12:30
			EPO; JPO;	, .
			DERWENT	
-	0	4395723.pn. and (control adj port)	USPAT;	2004/10/19
	İ		US-PGPUB;	12:30
			EPO; JPO;	
	1	·	DERWENT	1
1_	2	4395723.pn.	USPAT;	2004/10/19
-	_	1333723.p.m.	US-PGPUB;	12:30
1	·		EPO; JPO;	
			DERWENT	
	2	20020100265 mm	USPAT;	2004/10/19
-	2	20020190265.pn.	US-PGPUB;	12:31
			EPO; JPO;	12.31
			1	
			DERWENT	2004/10/10
-	0	20020190265.pn. and (control adj port)	USPAT;	2004/10/19
			US-PGPUB;	12:31
			EPO; JPO;	1
			DERWENT	1
-	0	438/268.ccls. and (thyristor same	USPAT;	2004/10/19
		semiconductor) and (doped adj emitter)	US-PGPUB;	12:36
1		and (doped adj well) and (control adj	EPO; JPO;	
		port)	DERWENT	
_	1	1 * .'	USPAT;	2004/10/19
	1	(thyristor same semiconductor) and (doped	US-PGPUB;	12:38
		adj emitter) and (doped adj well) and	EPO; JPO;	
		(control adj port)	DERWENT	
1_	1	1	USPAT;	2004/11/03
_	1	(thyristor same semiconductor) and (doped	US-PGPUB;	09:23
		adj emitter) and (doped adj well) and	EPO; JPO;	
			DERWENT	1
	_	(control adj port)		2004/10/19
-	0	438/134, 135, 136, 137, 138, 139, 140.ccls. and	USPAT;	
	'	(thyristor same semiconductor) and (doped	US-PGPUB;	12:57
		adj emitter) and (doped adj well) and	EPO; JPO;	[
		(control adj port)	DERWENT	1 2 2 2 4 2 2 4 2 2
-	4		USPAT;	2004/10/19
	ŀ	(thyristor same semiconductor) and	US-PGPUB;	12:58
	İ	(emitter) and (well) and (control adj	EPO; JPO;	. 1
	1	port)	DERWENT	
_	4	17	USPAT;	2004/10/19
	1	(thyristor same semiconductor) and	US-PGPUB;	12:59
		(emitter) and (well) and (control adj	EPO; JPO;	
1	1	port) and @ad<20021028	DERWENT	ļ
l _	4	15	USPAT;	2004/11/01
1 -	. ⁴	(thyristor same semiconductor) and	US-PGPUB;	13:33
			EPO; JPO;	13.33
		(emitter) and (well) and (control adj		
1	1	port) and @ad<20021028	DERWENT	<u> </u>

				******	0001/10/10
-	2	6756612.pn.		USPAT;	2004/10/19
		•		US-PGPUB;	15:49
				EPO; JPO;	
i			.	DERWENT	
_	2	6777271.pn.		USPAT;	2004/11/01
		•		US-PGPUB;	12:31
				EPO; JPO;	
				DERWENT	
1	1 1	6777271.pn. and anneal\$3		USPAT;	2004/11/01
-		6///2/1.pn. and annears		US-PGPUB;	13:18
					13:10
			i	EPO; JPO;	
				DERWENT	
-	1	6777271.pn. and anneal\$3 and (control a	adj	USPAT;	2004/11/01
		port)		US-PGPUB;	13:20
				EPO; JPO;	
1				DERWENT	
_	l ol	6777271.pn. and anneal\$3 and (control	adi	USPAT;	2004/11/01
		port) and (carrier adj coupler)	,	US-PGPUB;	13:20
		port, and (carrier ad) coupler,		EPO; JPO;	13.20
j			٠,.	DERWENT	2004/11/01
-	0		adj	USPAT;	2004/11/01
		port) and (carrier same drain\$3)		US-PGPUB;	13:22
				EPO; JPO;	l
				DERWENT	
-	l ol	6777271.pn. and anneal\$3 and (control	adj	USPAT;	2004/11/01
		port) and (carrier\$3 same drain\$3)	-	US-PGPUB;	13:22
				EPO; JPO;	
				DERWENT	
1	-	(777271 mm and annuals and (control	244	USPAT;	2004/11/01
-	1		auj	· ·	13:23
		port) and (contact same drain\$3)		US-PGPUB;	13:23
				EPO; JPO;	
				DERWENT	
-	89714	6777271.pn. (contact same drain\$3)		USPAT;	2004/11/01
				US-PGPUB;	13:25
		'		EPO; JPO;	
				DERWENT	
1 -	1	6777271.pn. and (contact same drain\$3)		USPAT;	2004/11/01
	_	(and the second		US-PGPUB;	13:25
		'		EPO; JPO;	•
				DERWENT	
. [0	6777271.pn. and (contact same drain\$3	and	USPAT;	2004/11/01
-		carrier\$3)		US-PGPUB;	13:26
		Callerasi		EPO; JPO;	13.20
	1				
				DERWENT	2004/11/01
-	0	6777271.pn. and (contact same drain\$3		USPAT;	2004/11/01
	!	same carrier\$3)		US-PGPUB;	13:26
				EPO; JPO;	
	1			DERWENT	
-	0	(thyristor same semiconductor) and		USPAT;	2004/11/01
		@ad<20021028 and (doped adj emitter) a	nd	US-PGPUB;	13:28
		(doped adj well) and (carrier\$3 same		EPO; JPO;	
		contact same drain\$3) and control		DERWENT	
_	0	(thyristor same semiconductor) and		USPAT;	2004/11/01
	1	@ad<20021028 and (doped adj emitter) a	nd	US-PGPUB;	13:28
		(doped adj well) and (carrier\$3 same		EPO; JPO;	
	1			DERWENT	
	_	contact same drain\$3)	222	1	2004/11/01
-	0	438/134, 135, 136, 137, 138, 139, 140.ccls.	and	USPAT;	2004/11/01
	Ţ	(thyristor same semiconductor) and		US-PGPUB;	13:34
		(trench) and (well) and (control adj		EPO; JPO;	
		port) and @ad<20021028 and carrier		DERWENT	
-	3	438/134,135,136,137,138,139,140.ccls.	and	USPAT;	2004/11/01
		(thyristor same semiconductor) and		US-PGPUB;	14:35
		(trench) and (well) and (control adj		EPO; JPO;	
		port) and @ad<20021028		DERWENT	
-	1 0	6653174.pn. and (doped adj well)		USPAT;	2004/11/01
				US-PGPUB;	14:37
		·		EPO; JPO;	1
				DERWENT	
		6653174 nn and //damed add 00111		USPAT;	2004/11/01
1	0	6653174.pn. and ((doped adj well) same	•	· ·	
1		carrier\$2)		US-PGPUB;	14:38
				EPO; JPO;	
				DERWENT	

	2	6548905.pn.	USPAT;	2004/11/01
	_	00.0300.F	US-PGPUB;	15:18
			EPO; JPO;	10110
			DERWENT	
_	1	257/180,163,156,155,133,134.ccls. and	USPAT;	2004/11/03
<u>'</u>	•	(thyristor same semiconductor) and (doped	US-PGPUB;	09:23
		adj emitter) and (doped adj well) and	EPO; JPO;	03.20
		(control adj port)	DERWENT	
_	1	257/180,163,156,155,133,134.ccls. and	USPAT;	2004/11/03
	1	(thyristor same semiconductor) and	US-PGPUB;	09:23
		(emitter) and (doped adj well) and	EPO; JPO;	03.23
		(control adj port)	DERWENT	
_	2	(thyristor same semiconductor) and	USPAT;	2004/11/03
	2	@ad<20021028 and (doped adj emitter) and	US-PGPUB;	09:25
		(doped adj well)	EPO; JPO;	03.23
		(doped ad) well)	DERWENT	
_	2	(thyristor same semiconductor) and	USPAT;	2004/11/03
	2	@ad<20021028 and (doped adj emitter) and	US-PGPUB;	09:49
		(doped adj well) and carrier\$2	EPO; JPO;	03.43
		(doped ad) well, and calllelyz	DERWENT	1
	0	(thyristor same semiconductor) and	USPAT;	2004/11/03
	U	@ad<20021028 and (doped adj emitter) and	US-PGPUB;	09:53
		(doped adj well) and (carrier\$2 same	EPO; JPO;	03.00
		drain\$3)	DERWENT	
_]	2	2002113267.pn.	USPAT;	2004/11/03
_	2	2002113207.pm.	US-PGPUB;	09:54
		·	EPO; JPO;	""
			DERWENT	
_	2	6498372.pn.	USPAT;	2004/11/03
	2	0130372.pii.	US-PGPUB;	09:56
			EPO; JPO;	
			DERWENT	
_	1	1989DE-3908281.PRAI,AP.	USPAT;	2004/11/03
		1505BB 5500Z01:11kAI/AI.	US-PGPUB;	09:59
			EPO; JPO;	
			DERWENT	1
_ '	1	2001US-0992629.PRAI,AP.	USPAT;	2004/11/03
		200105 0552025.11411/111.	US-PGPUB;	10:01
			EPO; JPO;	
j			DERWENT	1